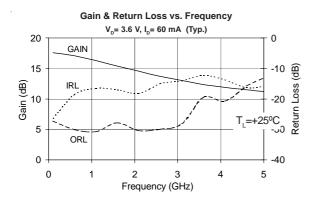


The SGA-5386 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring 1 micron emitters provides high FT and excellent thermal perfomance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction nonlinearities results in higher suppression of intermodulation products. Only 2 DC-blocking capacitors, a bias resistor and an optional RF choke are required for operation.

The matte tin finish on Sirenza's lead-free package utilizes a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. This package is also manufactured with green molding compounds that contain no antimony trioxide nor halogenated fire retardants.



SGA-5386



DC-5000 MHz, Cascadable **SiGe HBT MMIC Amplifier**



Product Features

- •Now available in Lead Free, RoHS Compliant, & Green Packaging
- High Gain: 14.9 dB at 1950 MHz
- Cascadable 50 Ohm
- Operates From Single Supply
- Low Thermal Resistance Package

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Symbol	Parameter	Units	Frequency	Min.	Тур.	Max.
G	Small Signal Gain	dB dB dB	850 MHz 1950 MHz 2400 MHz	15.2	16.6 14.9 14.0	18.3
P _{1dB}	Output Power at 1dB Compression	dBm dBm	850 MHz 1950 MHz		17.0 14.7	
OIP ₃	Output Third Order Intercept Point	dBm dBm	850 MHz 1950 MHz		32.0 29.0	
Bandwidth	Determined by Return Loss (>10dB)	MHz			5000	
IRL	Input Return Loss	dB	1950 MHz		18.5	
ORL	Output Return Loss	dB	1950 MHz		30.0	
NF	Noise Figure	dB	1950 MHz		4.0	
V_{D}	Device Operating Voltage	V		3.1	3.6	4.1
I _D	Device Operating Current	mA		54	60	66
R _{TH} , j-l	Thermal Resistance (junction to lead) °C/W 97					
$V_s = 8 V$ $I_D = 60 \text{ mA Typ.}$ OIP ₃ Tone Spacing = 1 MHz, Pout per tone = 0 dBm Test Conditions: R = 75 Ohms T = 25°C 7 = 7 = 50 Ohms						

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 $Z_s = Z_l = 50 \text{ Ohms}$

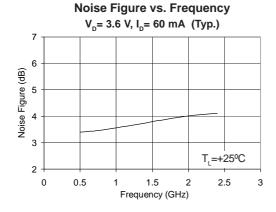
 $T_1 = 25^{\circ}C$

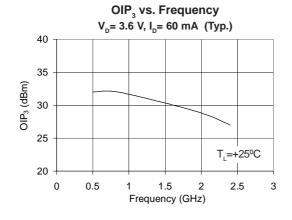
 $R_{BIAS} = 75 \text{ Ohms}$



Typical RF Performance at Key Operating Frequencies

				Frequency (MHz)					
Symbol	P	arameter	Unit	100	500	850	1950	2400	3500
G	Small Signal C	Gain	dB	17.6	17.2	16.6	14.7	14.0	12.5
OIP ₃	Output Third (Order Intercept Point	dBm		32.0	32.0	29.0	27.0	
P _{1dB}	Output Power	at 1dB Compression	dBm		17.0	17.0	14.7	13.6	
IRL	Input Return L	.oss	dB	26.4	19.6	16.9	18.5	15.8	11.6
ORL	Output Return	Loss	dB	27.3	29.5	31.0	30.0	33.4	19.1
S ₁₂	Reverse Isola	tion	dB	20.6	20.8	21.1	21.2	21.2	19.8
NF	Noise Figure		dB		3.4	3.5	4.0	4.1	
Test	Conditions:	3	$I_D = 60 I$ $T_1 = 25^\circ$	mA Typ. C	OIP_3 Tone $Z_1 = Z_1 = 50$	Spacing = 1	MHz, Pou	t per tone =	0 dBm



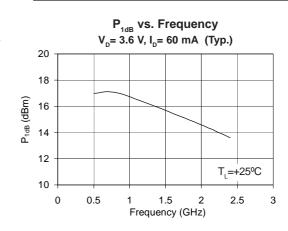


Absolute Maximum Ratings

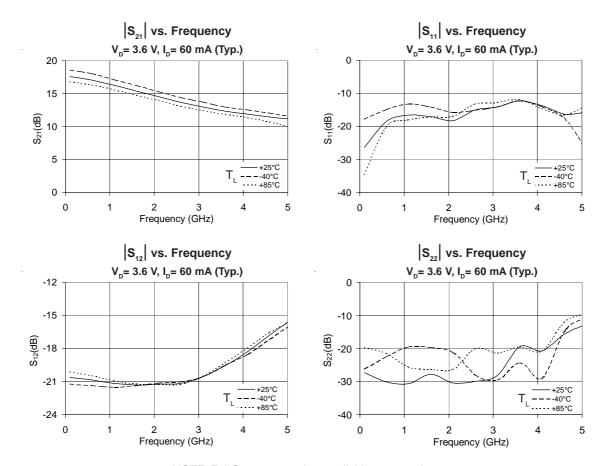
Parameter	Absolute Limit	
Max. Device Current (I _D)	120 mA	
Max. Device Voltage (V _D)	5 V	
Max. RF Input Power	+16 dBm	
Max. Junction Temp. (T _J)	+150°C	
Operating Temp. Range (T _L)	-40°C to +85°C	
Max. Storage Temp.	+150°C	

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias Conditions should also satisfy the following expression: $I_{_{D}}V_{_{D}}\!<(T_{_{J}}\!-\!T_{_{L}})\;/\;R_{_{TH'}}\;j\text{-}I$



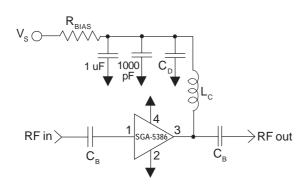


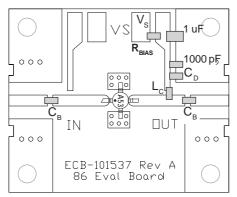


NOTE: Full S-parameter data available at www.sirenza.com

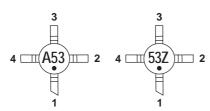


Basic Application Circuit





Part Identification Marking





Caution: ESD sensitive

Appropriate precautions in handling, packaging and testing devices must be observed.

See Application Note AN-075 for Package Outline Drawing

Application Circuit Element Values

Reference	Frequency (Mhz)						
Designator	500	850	1950	2400	3500		
C _B	220 pF	100 pF	68 pF	56 pF	39 pF		
C _D	100 pF	68 pF	22 pF	22 pF	15 pF		
L _c	68 nH	33 nH	22 nH	18 nH	15 nH		

Recommended Bias Resistor Values for I_p =60mA R_{BIAS} =(V_S - V_D) / I_D					
Supply Voltage(V _s)	6 V	8 V	10 V	12 V	
R _{BIAS} 39 Ω 75 Ω 110 Ω 150 Ω					
Note: R _{BIAS} provides DC bias stability over temperature.					

Mounting Instructions

- 1. Use a large ground pad area under device pins 2 and 4 with many plated through-holes as shown.
- We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick FR-4 board with 1 ounce copper on both sides.

Pin #	Function	Description
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.
2, 4	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance.
3	RF OUT/ BIAS	RF output and bias pin. DC voltage is present on this pin, therefore a DC blocking capacitor is necessary for proper operation.

Part Number Ordering Information

Part Number	Reel Size	Devices/Reel
SGA-5386	13"	3000
SGA-5386Z	13"	3000